



40V NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

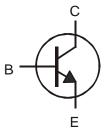
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT3906)
- Ideal for Medium Power Amplification and Switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

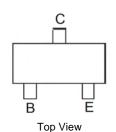
- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <a>3
- Weight: 0.008 grams (approximate)







Device Symbol



Pin-Out

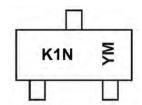
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3904-7-F	AEC-Q101	K1N / C1N	7	8	3,000
MMBT3904Q-7-F	Automotive	K1N	7	8	3,000
MMBT3904-13-F	AEC-Q101	K1N / C1N	13	8	10.000

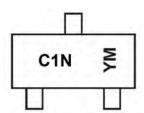
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

Marking Information



K = SAT (Shanghai Assembly / Test site)
1N = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: Y = 2011)
M = Month (ex: 9 = September)



C = CAT (Chengdu Assembly / Test site)
1N = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: Y = 2011)
M = Month (ex: 9 = September)

Date Code Key

Year	2010		2011	2012		2013	2014		2015	2016		2017
Code	Х		Υ	Z		Α	В		С	D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Continuous Collector Current	Ic	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	D	310	
Power Dissipation	(Note 7)	P _D	350	mW
Thermal Resistance, Junction to Ambient	(Note 6)	D	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	357	-0/00
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	350	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

Notes:

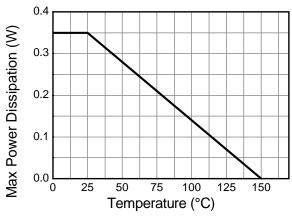
- 6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 7. For the device mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

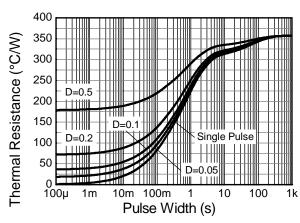
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



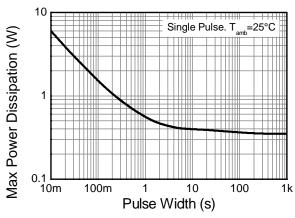
Thermal Characteristics





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation

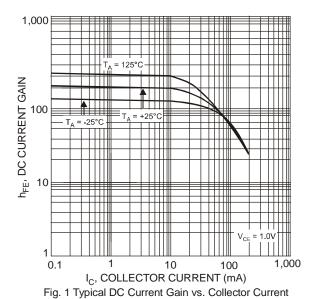


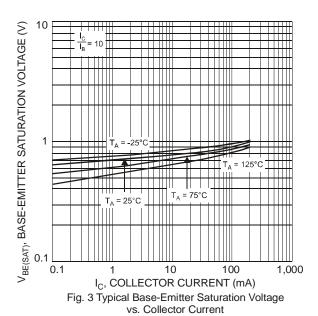
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

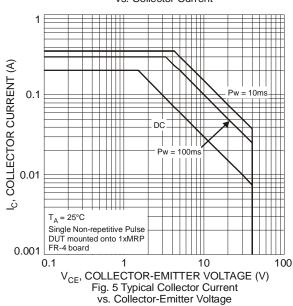
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	60		٧	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	40		٧	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0		V	$I_E = 10 \mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$
Base Cutoff Current	I _{BL}		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$
ON CHARACTERISTICS (Note 10)					
DC Current Gain	h _{FE}	40 70 100 60 30	 300 	_	$I_{C} = 100 \mu A$, $V_{CE} = 1.0 V$ $I_{C} = 1.0 mA$, $V_{CE} = 1.0 V$ $I_{C} = 10 mA$, $V_{CE} = 1.0 V$ $I_{C} = 50 mA$, $V_{CE} = 1.0 V$ $I_{C} = 100 mA$, $V_{CE} = 1.0 V$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.20 0.30	V	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.65	0.85 0.95	٧	$I_C = 10mA$, $I_B = 1.0mA$ $I_C = 50mA$, $I_B = 5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C_{ibo}	_	8.0	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$
Input Impedance	h _{ie}	1.0	10	kΩ	
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz
Output Admittance	h _{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f⊤	300	_	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz
Noise Figure	NF		5.0	dB	$V_{CE} = 5.0V$, $I_{C} = 100\mu A$, $R_{S} = 1.0k\Omega$, $f = 1.0kHz$
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Rise Time	t _r		35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	ts		200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	t _f	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.









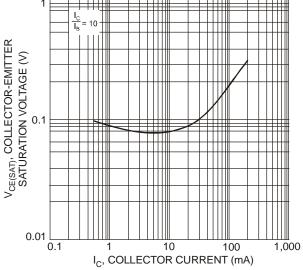


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

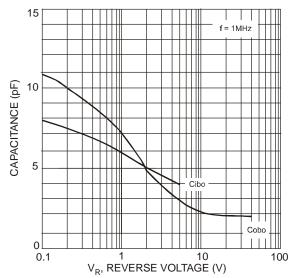
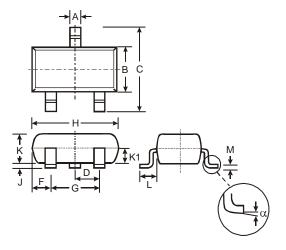


Fig. 4 Typical Capacitance Characteristics



Package Outline Dimensions

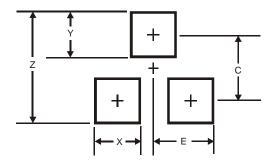
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
M	0.085	0.18	0.11					
α	0°	8°	-					
All	All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
Е	1.35



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